

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
26 April 2001 (26.04.2001)

PCT

(10) International Publication Number
WO 01/29890 A2

(51) International Patent Classification⁷: H01L 21/603

(21) International Application Number: PCT/SE00/02012

(22) International Filing Date: 17 October 2000 (17.10.2000)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
9903798-8 19 October 1999 (19.10.1999) SE
60/160,411 19 October 1999 (19.10.1999) US

(71) Applicant (for all designated States except US): IMEGO AB [SE/SE]; Aschebergsgatan 46, Byggnad 11, S-411 33 Göteborg (SE).

(72) Inventors; and

(75) Inventors/Applicants (for US only): BERGSTEDT, Leif [SE/SE]; Allmänna vägen 6, S-518 41 Sjömarken (SE). ANDERSONN, Gert [SE/SE]; Stockens väg, Pl. 2022, S-437 93 Lindome (SE). OTTOSSON, Britta [—/SE]; Dalgångsgatan 28, S-431 39 Mölndal (SE).

(74) Agent: GÖTEBORGS PATENTBYRÅ DAHLS AB; Sjöporten 4, S-417 64 Göteborg (SE).

(81) Designated States (*national*): AE, AG, AL, AM, AT, AT (utility model), AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CR, CU, CZ, CZ (utility model), DE, DE (utility model), DK, DK (utility model), DM, DZ, EE, EE (utility model), ES, FI, FI (utility model), GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KR (utility model), KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NO, NZ, PL, PT, RO, RU, SD, SE, SG, SI, SK, SK (utility model), SL, TJ, TM, TR, TT, TZ, UA, UG, US, UZ, VN, YU, ZA, ZW.

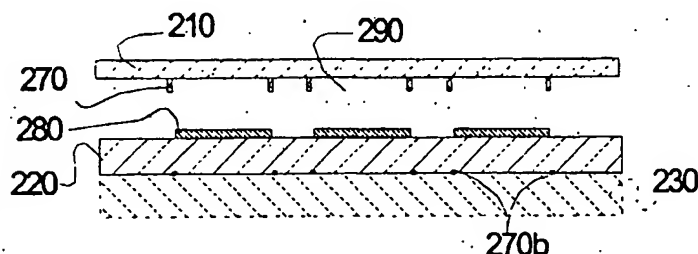
(84) Designated States (*regional*): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GW, ML, MR, NE, SN, TD, TG).

Published:

— Without international search report and to be republished upon receipt of that report.

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: METHOD RELATING TO ANODIC BONDING



(57) Abstract: The present invention relates to a method of bonding a first member (110, 210, 130, 230; 410, 430, 510, 530, 610) to a second silicon member (120; 220, 420a, 420b, 600) through anodic bonding. The method comprises the steps of selectively depositing on said first member bondable sections (170a, 170b, 270, 470a, 470b, 470c, 570, 620) before bringing said first and second members together for anodic bonding.

WO 01/29890 A2

TITLE

METHOD RELATING TO ANODIC BONDING

5 TECHNICAL FIELD OF THE INVENTION

The present invention relates to a method of bonding at least a first member to a second silicon member through anodic bonding.

10 BACKGROUND OF THE INVENTION

EP 742 581, for example, relates to a method of making sealed cavities on silicon wafer surfaces by anodic bonding and with electrically insulated conductors through the sealing areas to connect functional devices inside the cavities to electrical terminals outside said cavities. The
15 conductors are provided through the use of doped buried crossings in a single crystal silicon substrate, thereby also allowing production of different kinds of integrated silicon devices, e.g. sensors.

The technique implies that Borosilicate glass plates are bonded onto a silicon (Si) wafer using
20 so-called anodised bonding. A plate of glass is arranged on a Si wafer under an amount of pressure. The Si wafer and the glass are then heated up to some hundred degrees and a voltage is applied across the plates (glass and wafer) whereby the glass, which contains sodium (Na) ions migrate into the Si wafer, and a hermetic junction is obtained.

25 When two Si wafers are to be connected, a similar method as mentioned above is carried out, however, one of the wafers is coated with sputtered borosilicate glass and an anodised bonding is performed.

Generally, to be able to achieve an anodised bonding the object intended to be bonded to Si
30 must contain Na-ions, usually through doping a glass with Soda lime glass. The reason for using borosilicate glass is that it matches the Si wafer characteristics, specially with respect to

coefficient of expansion.

One major problem related to above mentioned and similar methods is the possibility of providing a conducting arrangement through the glass or wafer. In above mentioned European
5 Patent No. 742 581, for example, the electrical connection path is from one of an outside wire bonding area via a first contact diffusion down to a buried conductor which crosses below the sealing area of the cavity, and via a second contact diffusion to a second aluminium interconnection line which establishes connections to two piezo-resistors.

10 SUMMARY OF THE INVENTION

The main object of the present invention is to provide a method of providing a hermetical sealing between a first substrate and a silicon substrate.

15 Another object of the present invention is to achieve a hermetical sealing through selective deposition of bondable surfaces on a first substrate and the silicon substrate. Yet another object of the invention is to provide electrical connection between the sealed space and the outside environment through or under the sealing section.

20 For these reasons, the initially mentioned method comprises the steps of selectively depositing on said first member at least one bondable section before bringing said first and second members together for anodic bonding.

Preferably, the first member is a glass wafer, specially a borosilicate glass wafer and said
25 second wafer is a silicon wafer or the first member is a carrier wafer specially one of glass, ceramics or glass composite, such as LTCC (Low Temperature Cofired Ceramic) and said second wafer is a silicon wafer. The bondable section comprises a paste containing Na ions.

Preferably, the selective deposition is provided through screen printing or photo image forming.
30

Most preferably, depending on the function of the circuitry the bonding is hermetical.

Preferably, said first member comprises of a cover, that said second silicon member is a carrier for a functional device and said first member bonded to said second member provides a sealing for said functional device. Moreover, a third member is arranged as a carrying member for supporting said second member.

5

In one embodiment, electrical connections are arranged out of said cover through said bonding sections and/or said third supporting member.

Preferably, said connections through said bonding sections are arranged on one of said first,
10 second or third members before applying the bonding paste. The bonding sections are provided on said first member.

According to the invention, a method of selectively bonding a first member to a second silicon member through anodic bonding is provided, wherein the method comprises the steps of:
15 providing the said first and second members, arranging said first member with bonding sections in predetermined sections, arranging said first and second members in a contacting position, pressing and heating said first and second members in said contacting position, and applying a voltage to said first and second members. Preferably, the second member is a silicon wafer comprising one or more active sections. The first member is a glass wafer provided with frames
20 corresponding to said active sections.

The invention also concerns a sensor comprising a lid, a silicon substrate and a carrying substrate, wherein said lid, silicon substrate and carrying substrate are bonded through the method of the invention.

25

The invention also concerns a biological circuit hermetically connected to a substrate using the method of the invention.

BRIEF DESCRIPTION OF THE DRAWINGS

30

In the following, the invention will be further described in a non-limiting way with reference to

the accompanying drawings in which:

Fig. 1 schematically illustrates an arrangement produced according to the teachings of the invention,

5 Figs. 2a, 2b shows the wafers for anodic bonding process according to the invention in plan view,

Fig. 3 shows a cross-section along line III-III in figs. 2a and 2b, in a preassembled form,

10 Figs. 4a, 4b, 4c are cross-sections through different schematic embodiments showing wiring according to the invention,

Fig. 5 is a cross-section through yet another embodiment, and

Fig. 6 is a schematic cross-section through a device bonded according to another aspect of the invention.

15 DETAILED DESCRIPTION OF THE EMBODIMENTS

According to one preferred embodiment paste, e.g. of thick or thin film is through, e.g. screen printing or photo image forming, with doping containing Na ions, provided with conductive and non conductive sections which are bondable through anodic bonding. The carrier section may
20 be one of glass, ceramics or glass composite, such as LTCC (Low Temperature Cofired Ceramic).

There are a number of different thick-film pastes with different glass mixtures. It is also possible to produce pastes with sodium or soda-lime content, both as dielectric and conductive
25 pastes. However, the object of these is to provide a glass composition which matches the substrate to be printed.

Fig. 1 is a cross section through a device 100, e.g. a sensor according to above mentioned sensor of EP 742 581. The device comprises a cover or lid 110, e.g. of borosilicate glass or
30 other glass composition, a semiconducting wafer 120, a substrate 130, preferably a multi layer substrate including conductors 140 and vias 150 arranged therein and solder pads 160. The lid

110 is bonded to the Si wafer 120 through bonding areas 170a, provided in accordance with the teachings of the present invention. The substrate 130 is also bonded to the Si wafer 120 through bonding areas 170b, provided in accordance with the teachings of the present invention. The bonding areas 170 and 170b are provided as a paste on the lid 110 and carrier substrate 130, respectively, as closed frames through screen printing and/or photo image forming or the like.

The electronic circuitry or functional devices 180 arranged on the silicon (Si) wafer 120 are connected to the conductors 140, e.g. through connections 185 via the Si wafer. It is also possible to arrange connections that pass the bonding paste of the connection areas 170a and/or 170b, which will be exemplified in the following embodiments. The electronic circuitry 180 is further connected to other circuits through solder pads 160.

In a sensor, filter or similar applications both the lid 110 and the substrate 130 can be provided with cavities 190a and 190b, respectively.

Fig. 2a is a plane view of lid wafer 210 of glass on which a number of sealing frames 270 of a paste material containing Na-ions are printed, e.g. through screen printing. The frames provide a closed space building the cavities 290. On the other side, i.e. fig. 2b, functional devices 280 are realised on a Si wafer 220, which can be arranged on a carrying substrate 230 (fig. 3), which also is provided with bonding frames or sections 270b.

Fig. 3 illustrates the moment before the glass wafer 210 of fig. 2a is bonded onto the Si wafer 220 of fig. 2b. After the bonding process packaged units are formed, and each unit is cut out later in a suitable way well known for a skilled person.

In fig. 3, the functional devices 280 may also be countersunk in the substrate 220 through micro-machining or the like depending on the application and/or the material of the substrate.

The bonding process is performed in a known way, i.e. the Si wafer 220 and the lid glass wafer 210 or carrier 230 are combined and exposed to a pressure and heat up to a specific level, for example 350 °C (not limited) and then a voltage, e.g. 800 V (not limited), is applied through

the stack comprising the Si wafer and the lid wafer and/or the carrier.

Here, it is possible to provide different ways of electrical connections out of the functional devices arranged inside the sealed area on the semiconductive material 230: Firstly, according to fig. 1, i.e. through the carrying substrate 130 and secondly through the sealing frame 270/270b. In the embodiment of fig. 4a, a substrate 420a is provided with conductors 440a, e.g. through etching or the like. Then the paste 470a (thin film paste) applied onto the glass 410 is pressed on the substrate 420a.

10 In fig. 4b a thick-film paste 470b is applied through, e.g. screen printing onto the glass 410. Conductors 440b having substantially the same thickness as the paste are arranged through a suitable method on the substrate 430b, e.g. alumina.

Clearly, other embodiments are also possible as shown in fig. 4c, in which a substrate 430 of LTCC is used and into which conductors 440c are immersed. Paste 470c is applied onto the glass 410 before bonding.

As shown in fig. 5, it is also possible to countersink the pastes 570 into the substrate 530 of LTCC so that the upper surface of the paste comes into a substantially same level as the upper surface of the LTCC. The glass is denoted with 510.

Additionally, the bonding according to the invention can be used as a sealing in further applications. In fig. 6, for example, a so-called biological circuit 600 is connected to a substrate 610. The biological circuit comprises a conduit 601 for transporting fluid or gas. It is possible to connect and seal the circuit to an external substrate 610 of, e.g. LTCC of another circuit likewise provided with a conduit 611 using the teachings of the invention, i.e. arranging a ring shaped paste bonding means 620 and anodically bonding the circuit to the substrate or other circuits.

30 The invention is not limited the shown embodiments but can be varied in a number of ways without departing from the scope of the appended claims and the arrangement and the method

can be implemented in various ways depending on application, functional units, needs and requirements etc.

CLAIMS

1. Method of bonding at least a first member (110, 210, 130, 230, 410, 430, 510, 530, 610) to a second silicon member (120, 220, 420a, 420b, 600) through anodic bonding,
- 5 *characterised by*
- selectively depositing on said at least first member at least one bondable section (170a, 170b, 270, 470a, 470b, 470c, 570, 620) before bringing said first and second members together for anodic bonding.
- 10 2. The method according to claim 1,
- characterised in*
- that said first member (110, 210, 410, 510) is a glass wafer, specially a borosilicate glass wafer and said second wafer is a silicon wafer (120, 220, 420).
- 15 3. The method according to claim 1,
- characterised in*
- that said first member is a carrier wafer (130, 230, 430, 530) specially one of glass, ceramics or glass composite, such as LTCC (Low Temperature Cofired Ceramic) and said second wafer is a silicon wafer.
- 20 4. The method according to any of preceding claims,
- characterised in*
- that said bondable section (170a, 170b, 270, 470a, 470b, 470c, 570, 620) comprises a paste containing Na ions.
- 25 5. The method according to any of preceding claims,
- characterised in*
- that said selective deposition is provided through screen printing or photo image forming.
- 30 6. The method according to any of preceding claims,
- characterised in*

that said bonding is hermetical.

7. The method according to any of preceding claims,

characterised in

5 that said first member constitutes a cover, that said second silicon member is a carrier for a functional device (180, 280, 600) and said first member bonded to said second member provides a sealing for said functional device.

8. The method according claim 7,

10 *characterised in*

that a third member is arranged as a carrying member for supporting said second member.

9. The method according claim 7,

characterised in

15 that electrical connections out of said cover are arranged through said bonding sections.

10. The method according claim 8,

characterised in

that electrical connections out of said cover are arranged through said third supporting member.

20

11. The method according any of claims 8-10,

characterised in

that said connections through said bonding sections are arranged on one of said first, second or third members before applying the bonding paste.

25

12. The method according to any of preceding claims,

characterised in

that said bonding sections are provided on said first member.

30 13. A method of selectively bonding a first member (110, 210, 130, 230, 410, 430, 510, 530, 610) to a second silicon member (120, 220, 420a, 420b, 600) through anodic bonding,

characterised in

that said bonding method comprises the steps of:

- providing the said first and second members,
- arranging said first member with bonding sections in predetermined sections,
- 5 – arranging said first and second members in a contacting position,
- pressing and heating said first and second members in said contacting position, and
- applying a voltage to said first and second members.

14. The method according to claim 13,

10 *characterised in*

that second member is a silicon wafer comprising one or more active sections.

15. The method according to claim 14,

characterised in

15 that said first member is a glass wafer provided with frames corresponding to said active sections.

16. A sensor (100) comprising a lid (110), a silicon substrate (120), a carrying substrate (130) and sensor electronics, wherein said lid (110), silicon substrate (120) and carrying substrate

20 (130) are bonded through one or several of methods according to any one of claims 1-15.

17. A biological circuit (600) hermetically connected to a substrate (610) using one or several of methods according to any one of claims 1-15.

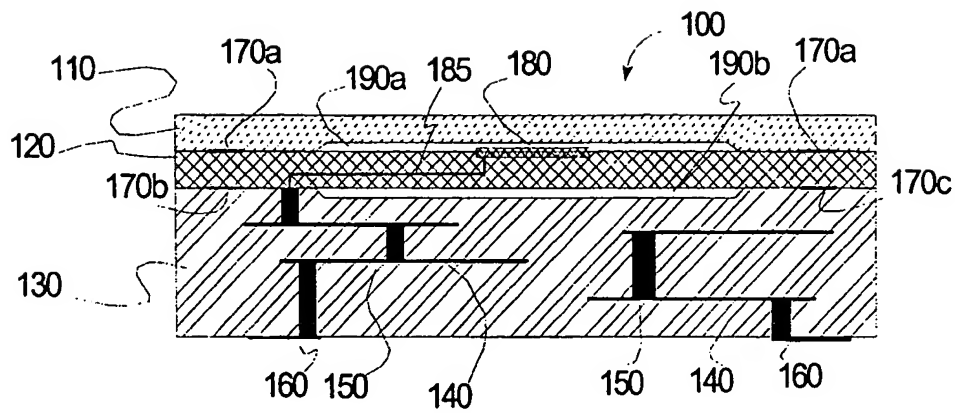


Fig. 1

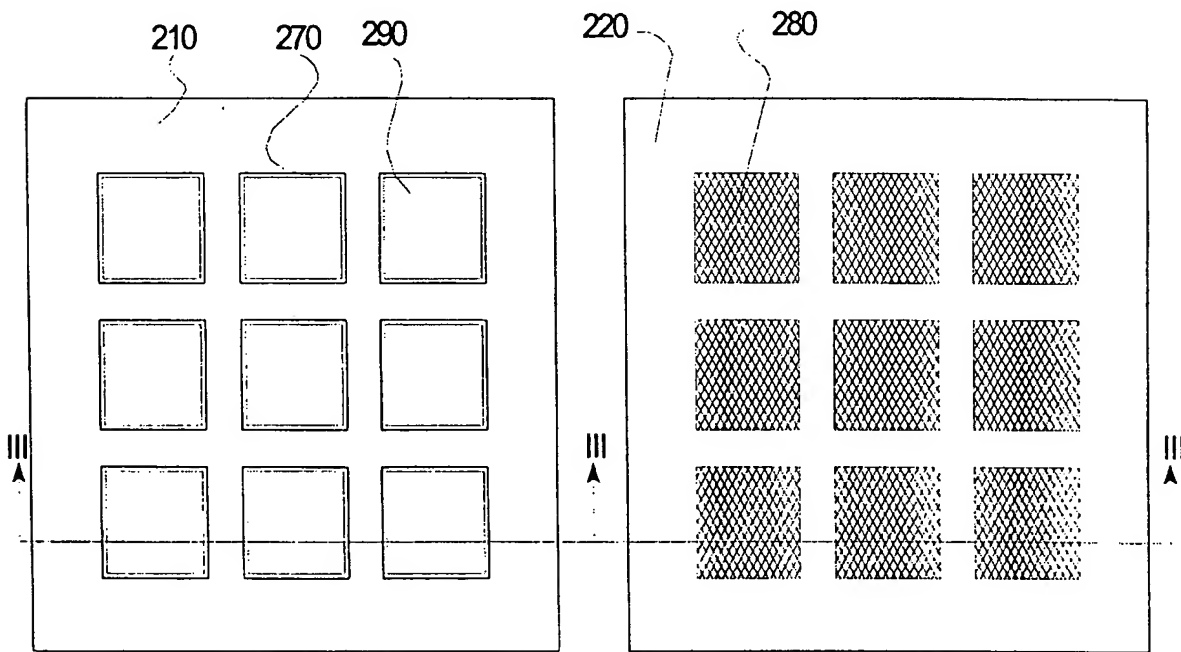


Fig. 2a

Fig. 2b

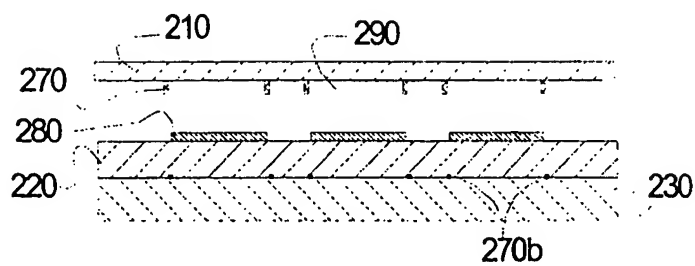


Fig. 3

2/3

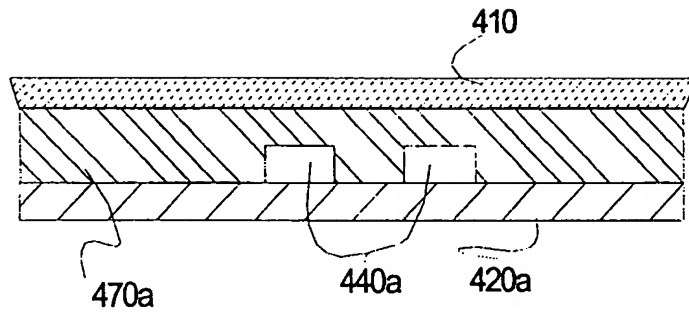


Fig. 4a

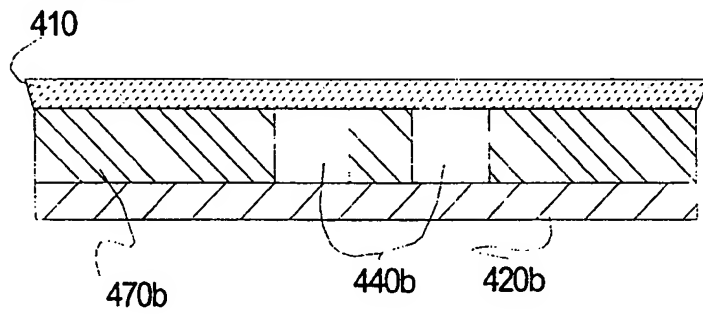


Fig. 4b

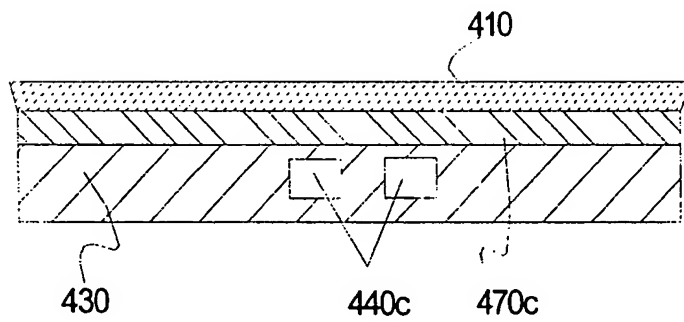


Fig. 4c

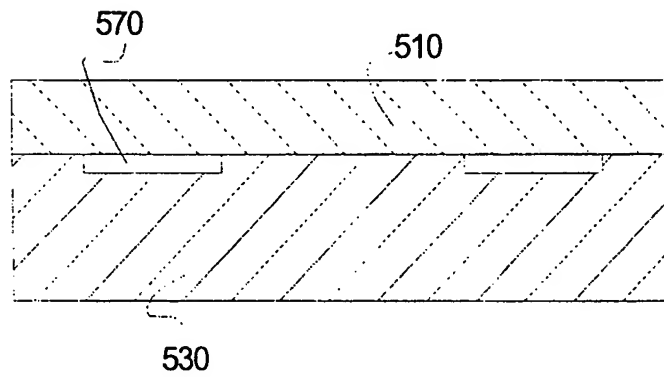


Fig. 5

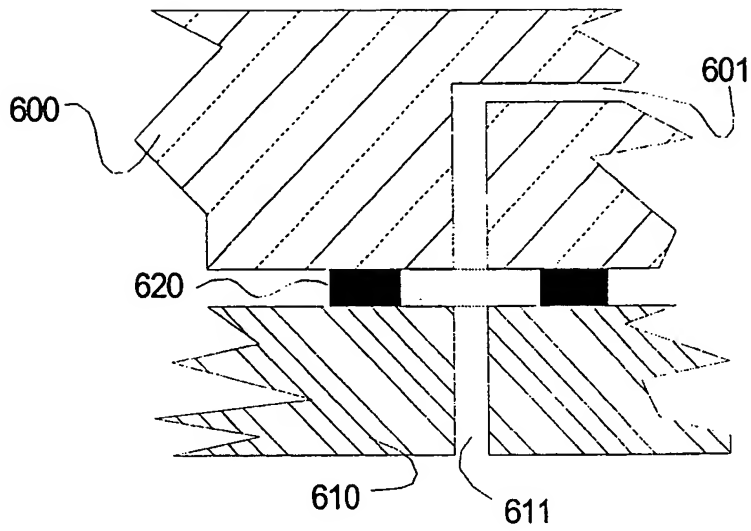


Fig. 6